

N-Channel Enhancement Mode Power MOSFET

Description

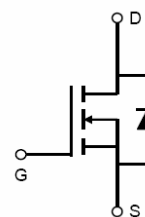
The HM2302F uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

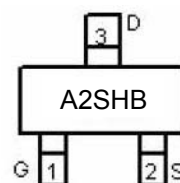
- $V_{DS} = 20V, I_D = 2.8A$
 $R_{DS(ON)} < 50m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 40m\Omega @ V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A2SHB	HM2302F	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	2.8	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	11	A
Maximum Power Dissipation	P_D	0.9	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	139	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.65	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=2.5V, I_D=2.8A$	-	30	40	m Ω
		$V_{GS}=4.5V, I_D=3A$	-	37	50	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=3A$	-	8	-	S
Dynamic Characteristics <small>(Note4)</small>						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	260	-	PF
Output Capacitance	C_{oss}		-	48	-	PF
Reverse Transfer Capacitance	C_{rss}		-	27	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=3.3\Omega$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	2.5	-	nS
Turn-on Rise Time	t_r		-	3.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	21	-	nS
Turn-Off Fall Time	t_f		-	3	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=3A,$ $V_{GS}=4.5V$	-	2.9	5	nC
Gate-Source Charge	Q_{gs}		-	0.4	-	nC
Gate-Drain Charge	Q_{gd}		-	0.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V_{SD}	$V_{GS}=0V, I_S=2.8A$	-	0.75	1.2	V
Diode Forward Current <small>(Note 2)</small>	I_S		-	-	2.8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

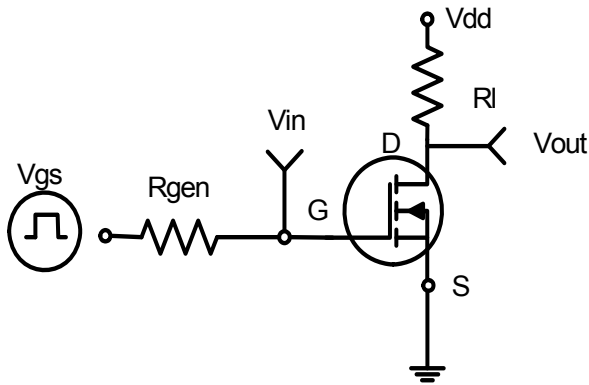


Figure 1: Switching Test Circuit

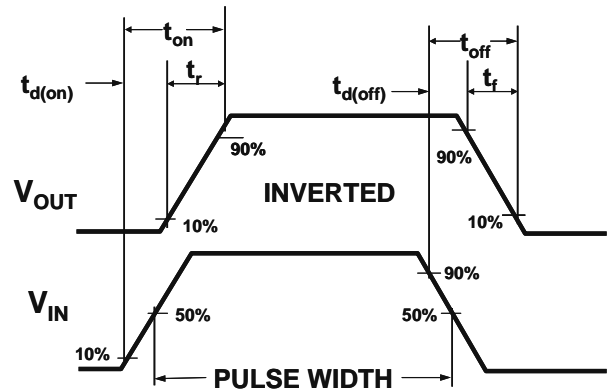
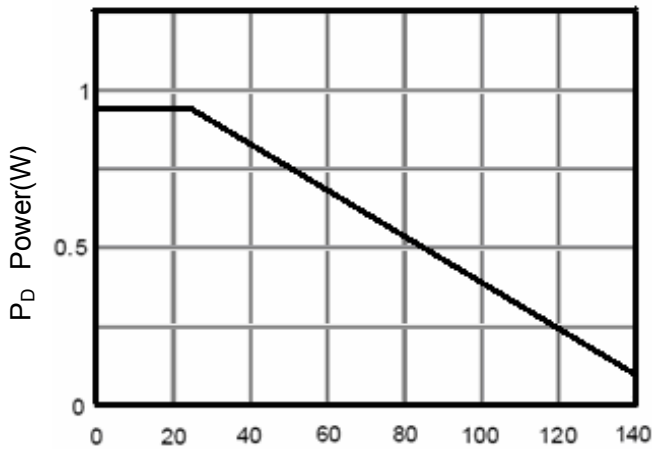
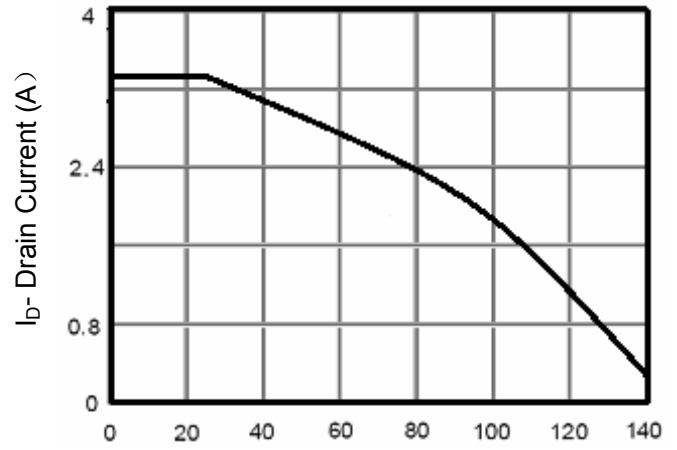


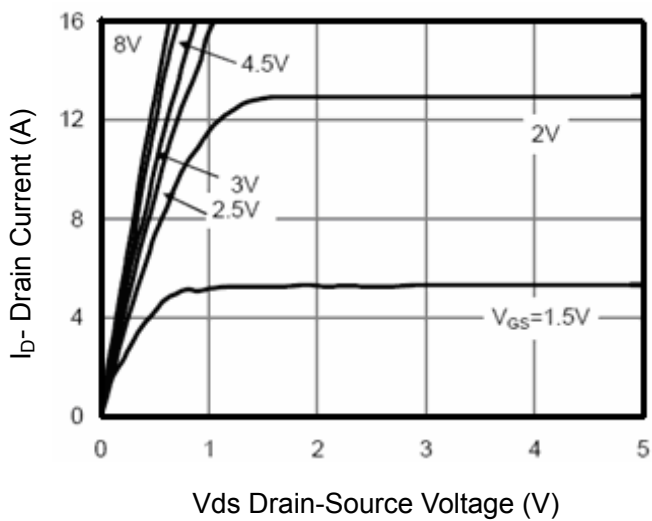
Figure 2: Switching Waveforms



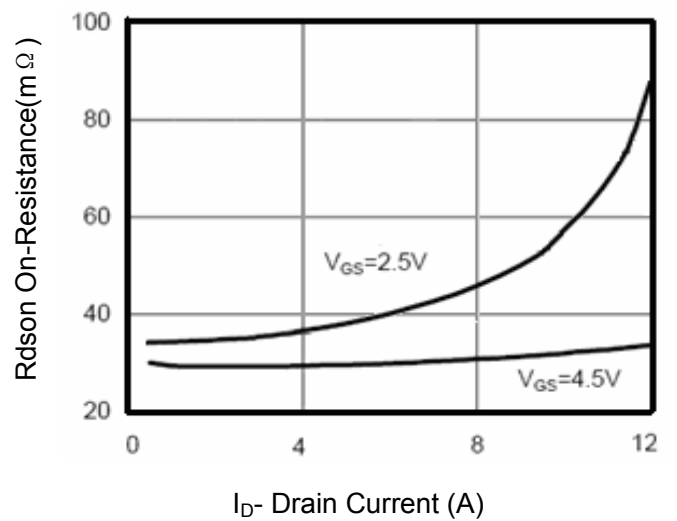
T_J-Junction Temperature(°C)
 Figure 3 Power Dissipation



T_J-Junction Temperature(°C)
 Figure 4 Drain Current



V_{DS} Drain-Source Voltage (V)
 Figure 5 Output Characteristics



I_D- Drain Current (A)
 Figure 6 Drain-Source On-Resistance

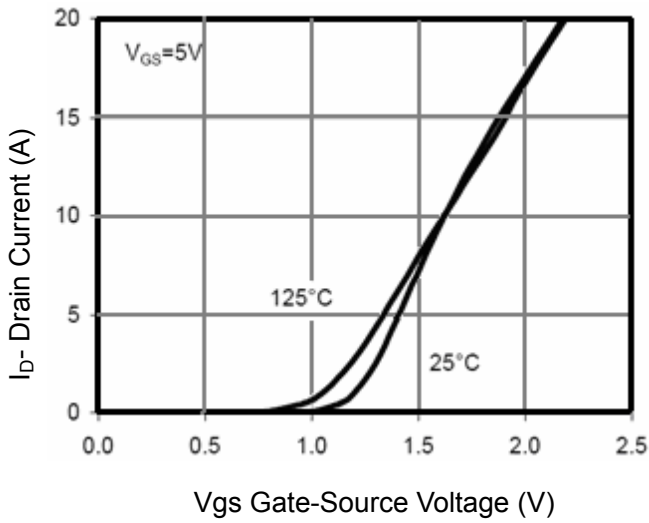


Figure 7 Transfer Characteristics

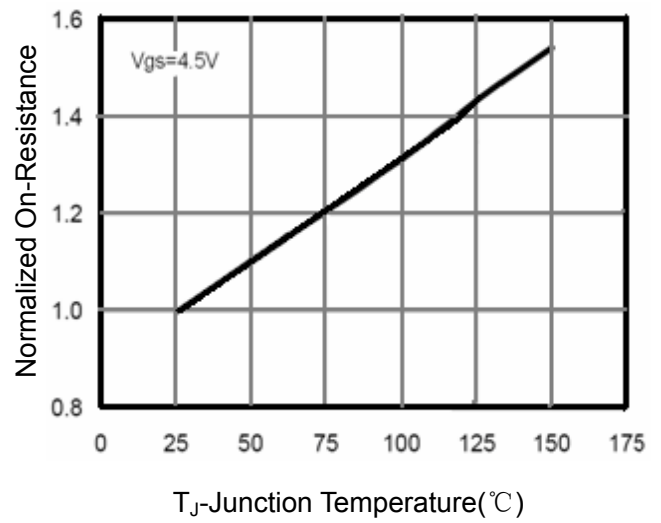


Figure 8 Drain-Source On-Resistance

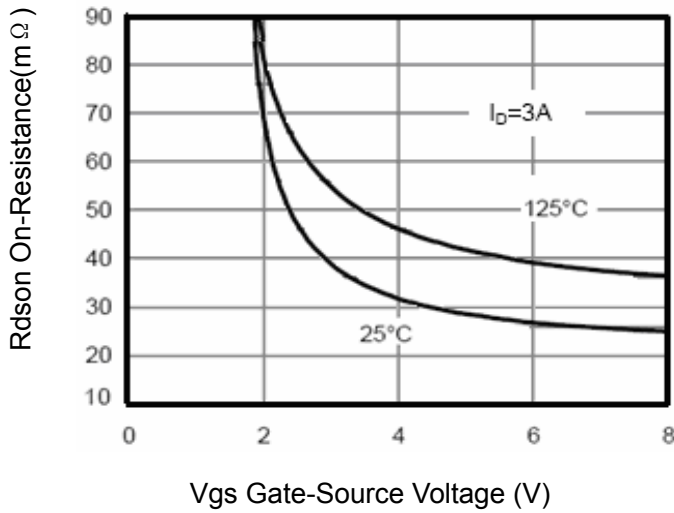


Figure 9 Rdson vs Vgs

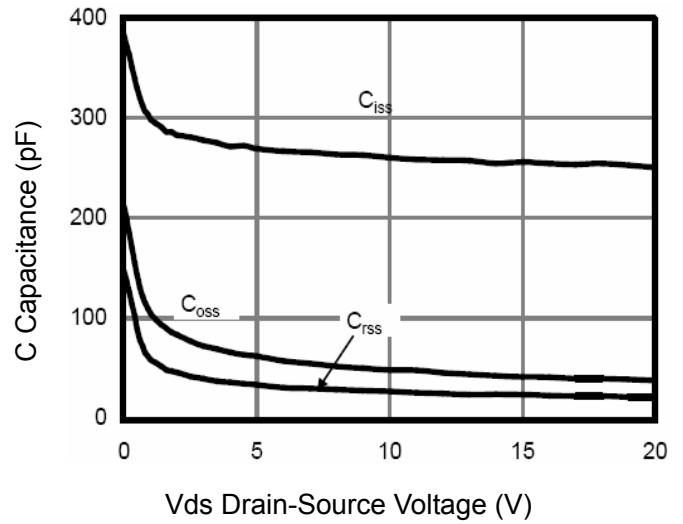


Figure 10 Capacitance vs Vds

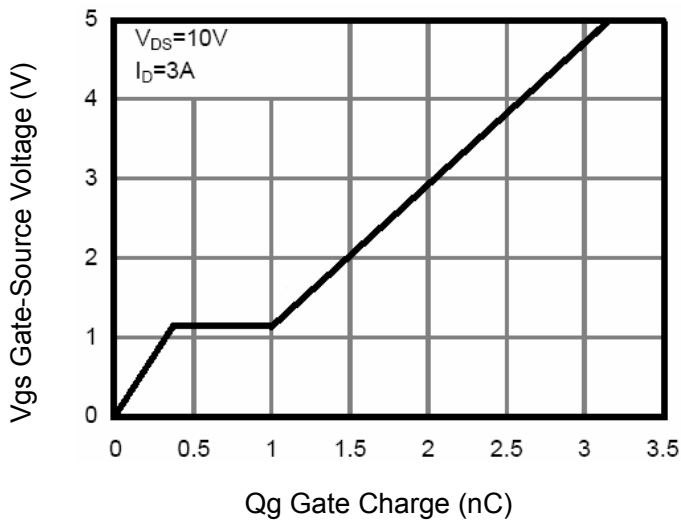


Figure 11 Gate Charge

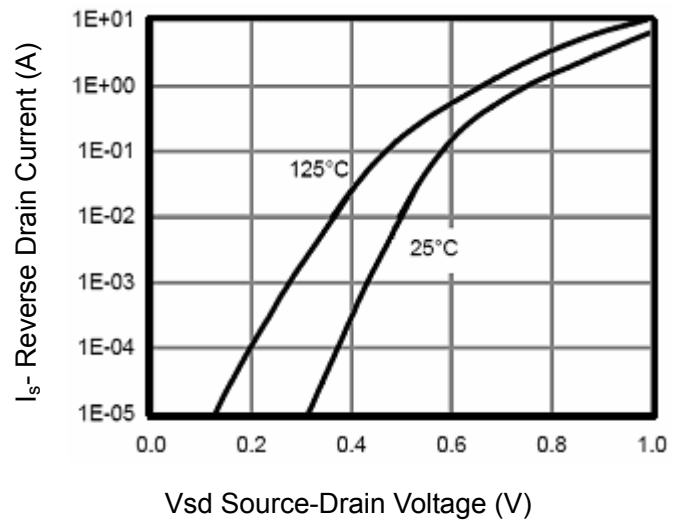


Figure 12 Source- Drain Diode Forward

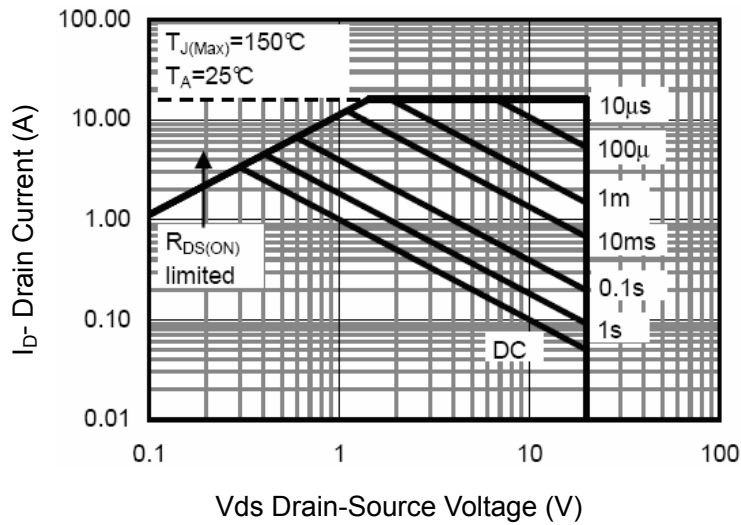


Figure 13 Safe Operation Area

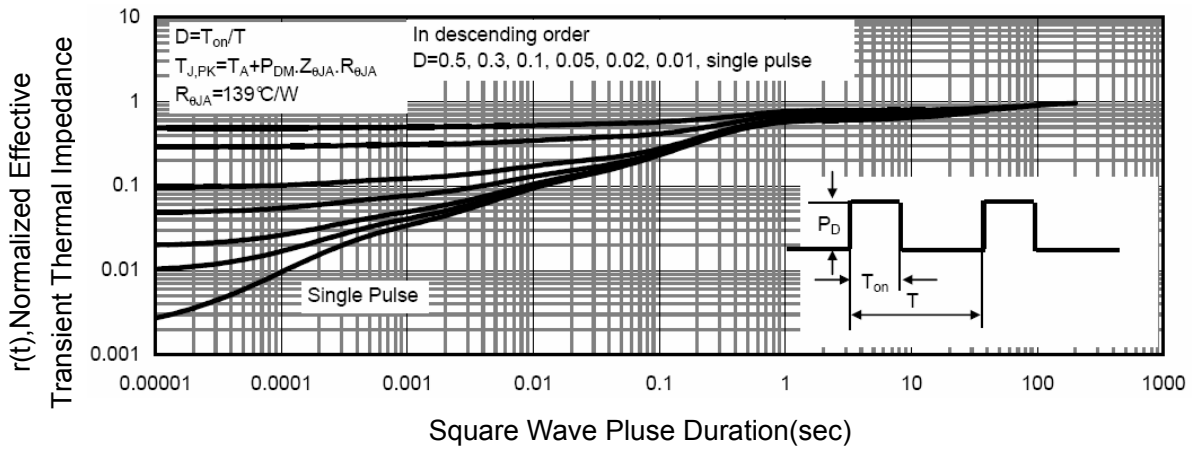
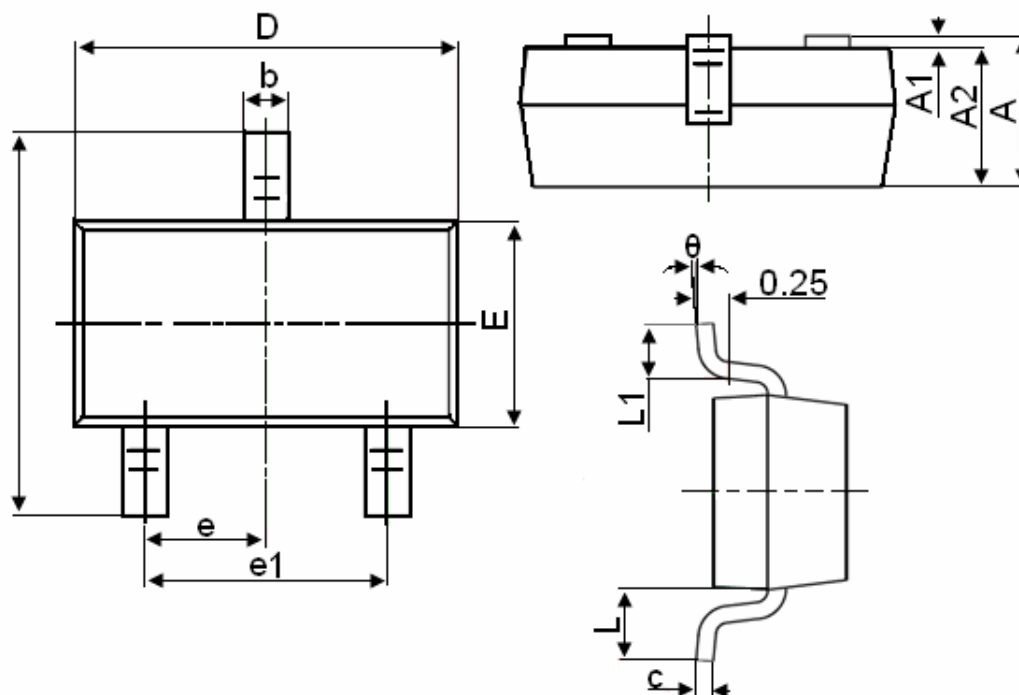


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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